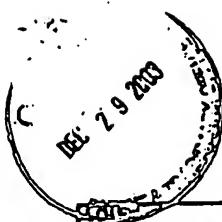




SHEET 1 OF 1

<b>FORM PTO - 1449</b> <b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>					<b>ATTORNEY DOCKET NO.: ASC-058A</b> <b>APPLICANTS: Leitz <i>et al.</i></b> <b>SERIAL NO.: 10/647,074</b> <b>FILING DATE: August 22, 2003</b> <b>GROUP: 2812- 2823</b>				
<b>U.S. PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
<i>Le</i>	A176	5,387,796	02/07/1995	Joshi <i>et al.</i>	/	/			
<i>Le</i>	A177	5,434,102	07/18/1995	Watanabe <i>et al.</i>	/	/			
<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Le</i>	B49	2-210816	08/22/1990	JP	/	/	N	Abstract	
<i>Le</i>	B50	3-36717	02/18/1991	JP	/	/	N	Abstract	
<i>Le</i>	B51	61-14116	06/28/1986	JP	/	/	N	Abstract	
<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>									
EXAM. INIT.	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>								
<i>Le</i>	C132	Feichtinger <i>et al.</i> , "Misfit Dislocation Nucleation Study in p/p+ Silicon," <u>Journal of the Electrochemical Society</u> , 148 (7) (2001), pp. G379-G382.							
	C133	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (April 15, 2002), pp. 4891-4899.							
	C134	Hsu <i>et al.</i> , "Surface morphology of related Ge <sub>x</sub> Si <sub>1-x</sub> films," <u>Applied Physics Letters</u> , 61 (11) (September 14, 1992), pp. 1293-1295.							
<i>Le</i>	C135	"How to Make Silicon," Wacker University, <a href="http://www.wafernet.com/PresWK/h-ptl-as3_wsc_siltronics_com_pages_training_pages_Silic...">http://www.wafernet.com/PresWK/h-ptl-as3_wsc_siltronics_com_pages_training_pages_Silic...</a> , August 28, 2002.							
EXAMINER <i>Le</i>				DATE CONSIDERED 9/23/04					

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## INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

APPLICANT(S): Leitz *et al.*

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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	A1	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A2	2001/0014570	08/16/2001	Wenski <i>et al.</i>			
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A4	2002/0052084	05/02/2002	Fitzgerald			
	A5	2002/0084000	07/04/2002	Fitzgerald			
	A6	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A7	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A8	2002/0123167	09/05/2002	Fitzgerald			
	A9	2002/0123183	09/05/2002	Fitzgerald			
	A10	2002/0123197	09/05/2002	Fitzgerald <i>et al.</i>			
	A11	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A12	2002/0125497	09/12/2002	Fitzgerald			
	A13	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A14	2002/0185686	12/12/2002	Christiansen <i>et al.</i>			
	A15	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A16	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A17	2003/0025131	02/06/2003	Lee <i>et al.</i>			
	A18	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A19	2003/0041798	03/06/2003	Wenski <i>et al.</i>			
	A20	2003/0057439	03/27/2003	Fitzgerald			
	A21	2003/0077867	04/24/2003	Fitzgerald			
	A22	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A23	2003/0127646	07/10/2003	Christiansen <i>et al.</i>			
<i>Lee</i>	A24	2003/0186073	10/02/2003	Fitzgerald			03/18/2003
<i>Lee</i>	A25	4,040,045	03/01/1977	Ruehrwein			
EXAMINER <i>Lee</i>				DATE CONSIDERED	<i>9/23/04</i>		



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ATTORNEY DOCKET NO.: ASC-058A

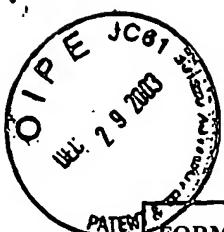
APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812-2823

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	A26	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A27	4,900,372	12/13/1990	Lee <i>et al.</i>			
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A29	4,990,979	02/05/1991	Otto			
	A30	4,997,776	03/05/1991	Harami <i>et al.</i>			
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A32	5,091,767	02/25/1992	Bean <i>et al.</i>			
	A33	5,097,630	03/24/1992	Maeda <i>et al.</i>			
	A34	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A35	5,159,413	10/27/1992	Calviello <i>et al.</i>			
	A36	5,166,084	11/24/1992	Pfiester			
	A37	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A38	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A39	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A40	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A41	5,210,052	05/11/1993	Takasaki			
	A42	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A43	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A44	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A45	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A46	5,252,173	10/12/1993	Inoue			
	A47	5,279,687	01/18/1994	Tuppen <i>et al.</i>			
	A48	5,285,086	02/08/1994	Fitzgerald			
	A49	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
<i>Lee</i>	A50	5,298,452	03/29/1994	Meyerson			
<i>Lee</i>	A51	5,308,444	05/03/1994	Fitzgerald <i>et al.</i>			
EXAMINER <i>R. Lee</i>				DATE CONSIDERED	9/23/04		



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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	A52	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A53	5,316,958	05/31/1994	Meyerson			
	A54	5,346,848	09/13/1994	Grupen-Shemansky <i>et al.</i>			
	A55	5,374,564	12/20/1994	Bruel			
	A56	5,399,522	03/21/1995	Ohori			
	A57	5,413,679	05/09/1995	Godbey			
	A58	5,424,243	06/13/1995	Takasaki			
	A59	5,425,846	06/20/1995	Koze <i>et al.</i>			
	A60	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A61	5,426,316	06/20/1995	Mohammad			
	A62	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A63	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A64	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A65	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A66	5,476,813	12/19/1995	Naruse			
	A67	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A68	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A69	5,523,243	06/04/1996	Mohammad			
	A70	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A71	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A72	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A73	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A74	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A75	5,617,351	04/01/1997	Bertin <i>et al.</i>			
	A76	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A77	5,633,516	05/27/1997	Mishima <i>et al.</i>			
<i>Lee</i>	A78	5,659,187	08/19/1997	Legoues <i>et al.</i>			
EXAMINER		DATE CONSIDERED		9/23/04			



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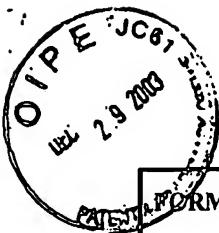
APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812-2823

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	A79	5,683,934	11/04/1997	Candelaria			
<i>Lee</i>	A80	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A81	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A82	5,728,623	03/17/1998	Mori			
	A83	5,739,567	04/14/1998	Wong			
	A84	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A85	5,777,347	07/07/1998	Bartelink			
	A86	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A87	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A88	5,792,679	08/11/1998	Nakato			
	A89	5,801,085	09/01/1998	Kim <i>et al.</i>			
	A90	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A91	5,810,924	09/22/1998	Legoues <i>et al.</i>			
	A92	5,828,114	10/27/1998	Kim <i>et al.</i>			
	A93	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A94	5,859,864	01/12/1999	Jewell			
	A95	5,877,070	03/02/1999	Goesele <i>et al.</i>			
	A96	5,891,769	04/06/1999	Liaw <i>et al.</i>			
	A97	5,906,708	05/25/1999	Robinson <i>et al.</i>			
	A98	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A99	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A100	5,943,560	08/24/1999	Chang <i>et al.</i>			
	A101	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A102	5,966,622	10/12/1999	Levine <i>et al.</i>			
	A103	5,998,807	12/07/1999	Lustig <i>et al.</i>			
	A104	6,010,937	01/04/2000	Karam <i>et al.</i>			
	A105	6,013,134	01/11/2000	Chu <i>et al.</i>			
<i>Lee</i>	A106	6,030,884	02/29/2000	Mori			
<i>Lee</i>	A107	6,033,974	03/07/2000	Henley <i>et al.</i>			
EXAMINER <i>H</i> <i>Lee</i>				DATE CONSIDERED			9/23/04



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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	A108	6,033,995	03/07/2000	Muller			
	A109	6,039,803	03/21/2000	Fitzgerald <i>et al.</i>			
	A110	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A111	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A112	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A113	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A114	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A115	6,107,653	08/22/2000	Fitzgerald			
	A116	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A117	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A118	6,124,614	09/26/2000	Ryum <i>et al.</i>			
	A119	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A120	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A121	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A122	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A123	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A124	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A125	6,160,303	12/12/2000	Fattaruso			
	A126	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A127	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A128	6,191,006	02/20/2001	Mori			
	A129	6,191,007	02/20/2001	Matsui <i>et al.</i>			
	A130	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A131	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A132	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A133	6,207,977	03/27/2001	Augusto			
	A134	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A135	6,218,677	04/17/2001	Broekaert			
<i>Lee</i>	A136	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
<i>Lee</i>	A137	6,235,567	05/22/2001	Huang			
EXAMINER <i>Lee</i>				DATE CONSIDERED	<i>9/23/04</i>		



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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>	A138	6,242,324	06/05/2001	Kub et al.			
	A139	6,249,022	06/19/2001	Lin et al.			
	A140	6,251,755	06/26/2001	Furukawa et al.			
	A141	6,261,929	07/17/2001	Gehrke et al.			
	A142	6,266,278	07/24/2001	Harari et al.			
	A143	6,271,551	08/07/2001	Schmitz et al.			
	A144	6,271,726	08/07/2001	Fransis et al.			
	A145	6,291,321	09/18/2001	Fitzgerald			
	A146	6,313,016	11/06/2001	Kibbel et al.			
	A147	6,316,301	11/13/2001	Kant			
	A148	6,323,108	11/27/2001	Kub et al.			
	A149	6,329,063	12/11/2001	Lo et al.			
	A150	6,335,546	01/01/2002	Tsuda et al.			
	A151	6,339,232	01/15/2002	Takagi			
	A152	6,350,993	02/26/2002	Chu et al.			
	A153	6,368,733	04/09/2002	Nishinaga			
	A154	6,372,356	04/16/2002	Thornton et al.			
	A155	6,399,970	06/04/2002	Kubo et al.			
	A156	6,403,975	06/11/2002	Brunner et al.			
	A157	6,406,589	06/18/2002	Yanagisawa			
	A158	6,407,406	06/18/2002	Tezuka			
	A159	6,420,937	07/16/2002	Akatsuka et al.			
	A160	6,425,951	07/30/2002	Chu et al.			
	A161	6,429,061	08/06/2002	Rim			
	A162	6,482,749	11/19/2002	Billington et al.			
	A163	6,503,773	01/07/2003	Fitzgerald			
	A164	6,515,335	02/04/2003	Christiansen et al.			
<i>Lee</i>	A165	6,518,644	02/11/2003	Fitzgerald			
EXAMINER <i>Lee</i>				DATE CONSIDERED <i>9/23/04</i>			

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ATTORNEY DOCKET NO.: ASC-058A

APPLICANT(S): Leitz et al.

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812 2823

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Lee</i>		A166 6,521,041	02/18/2003	Wu et al.			
<i>Lee</i>		A167 6,525,338	02/25/2003	Mizushima et al.			
<i>Lee</i>		A168 6,555,839	04/29/2003	Fitzgerald			
<i>Lee</i>		A169 6,573,126	06/03/2003	Cheng et al.			
<i>Lee</i>		A170 6,576,532	06/10/2003	Jones et al.			
<i>Lee</i>		A171 6,583,015	06/24/2003	Fitzgerald et al.			
<i>Lee</i>		A172 6,593,191	07/15/2003	Fitzgerald			
<i>Lee</i>		A173 6,594,293	07/15/2003	Bulsara et al.			
<i>Lee</i>		A174 6,602,613	08/05/2003	Fitzgerald			
<i>Lee</i>		A175 6,603,156	08/05/2003	Rim			

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Lee</i>		B1 41 01 167	07/23/1992	DE				N	Abstract
		B2 0 514 018	11/19/1992	EP				N	Y
		B3 0 587 520	03/16/1994	EP				N	Y
		B4 0 683 522	11/22/1995	EP				N	Y
		B5 0 828 296	03/11/1998	EP				N	Y
		B6 0 829 908	03/18/1998	EP				N	Y
		B7 0 838 858	04/29/1998	EP				N	Abstract
		B8 1 020 900	07/19/2000	EP				N	Y
		B9 1 174 928	01/23/2002	EP				N	Y
		B10 2 342 777	04/19/2000	GB				Y	Y
<i>Lee</i>		B11 4-307974	10/30/1992	JP				N	Abstract

EXAMINER *Lee*DATE CONSIDERED *9/23/04*



PATE FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT					ATTORNEY DOCKET NO.: ASC-058A APPLICANT(S): Leitz et al. SERIAL NO.: 10/647,074 FILING DATE: August 22, 2003 GROUP: 2012-2827				
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Lee</i>	B12	5-166724	07/02/1993	JP				N	Abstract
	B13	6-177046	06/24/1994	JP				N	Abstract
	B14	6-244112	09/02/1994	JP				Y	Y
	B15	6-252046	09/09/1994	JP				Y	Y
	B16	7-94420	04/07/1995	JP				N	Abstract
	B17	7-106446	04/21/1995	JP				N	Abstract
	B18	7-240372	09/12/1995	JP				N	Abstract
	B19	10-270685	10/09/1998	JP				N	Y
	B20	11-233744	08/27/1999	JP				N	Abstract
	B21	63-73398	04/02/1988	JP				N	N
	B22	2000-021783	01/21/2000	JP				N	Y
	B23	2000-031491	01/28/2000	JP				N	Y
	B24	2000-513507	10/10/2000	JP				Y	Y
	B25	2001-319935	11/16/2001	JP				N	Y
	B26	2002-076334	03/15/2002	JP				N	Y
	B27	2002-164520	06/07/2002	JP				N	Y
	B28	2002-289533	10/04/2002	JP				N	Y
	B29	2002-356399	12/13/2002	JP				N	Y
	B30	2003-520444	07/02/2003	JP				N	Abstract
	B31	98/59365	12/30/1998	WO				N	Y
	B32	99/53539	10/21/1999	WO				N	Y
	B33	00/48239	08/17/2000	WO				N	Y
	B34	00/54338	09/14/2000	WO				N	Y
	B35	01/022482	03/29/2001	WO				N	Y
<i>Lee</i>	B36	01/54175	07/26/2001	WO				N	Y
EXAMINER <i>Lee</i>					DATE CONSIDERED <i>9/23/04</i>				

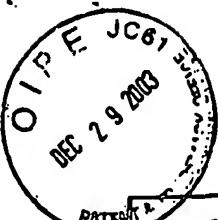


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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
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	B38	01/93338	12/06/2001	WO				N	Y
	B39	01/99169	12/27/2001	WO				N	Y
	B40	02/071488	09/12/2002	WO				N	Y
	B41	02/071491	09/12/2002	WO				N	Y
	B42	02/071495	09/12/2002	WO				N	Y
	B43	02/082514	10/17/2002	WO				N	Y
	B44	02/13262	02/14/2002	WO				N	Y
	B45	02/15244	02/21/2002	WO				N	Y
	B46	02/27783	04/04/2002	WO				N	Y
	B47	02/47168	06/13/2002	WO				N	Y
<i>Lee</i>	B48	03/015140	02/20/2003	WO				N	Y

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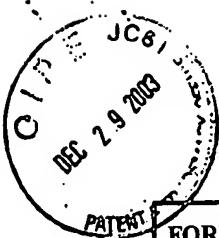
APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003 GROUP: 2812-2823

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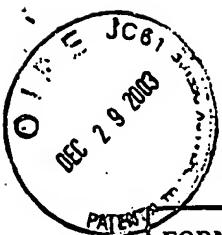
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
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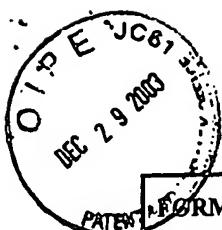
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SERIAL NO.: 10/647,074

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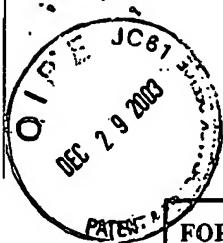
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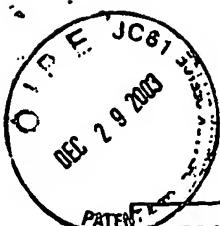
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
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FORM PTO - 1449

## INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

APPLICANT(S): Leitz *et al.*

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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)
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EXAMINER

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